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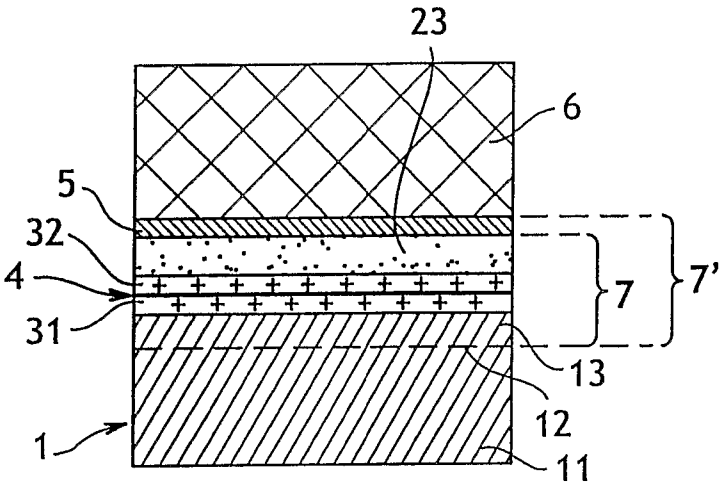
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(54) Title: A METHOD OF FABRICATING AN EPITAXIALLY GROWN LAYER




(57) Abstract: The invention concerns a method of fabricating an epitaxially grown layer (6). This method is remarkable in that it comprises the following steps consisting in : a) implanting atomic species within a support substrate (1) to define therein a zone of weakness (12) which demarcates a thin support layer (13) from the remainder (11) of said substrate; b) growing said epitaxial layer (6) by epitaxial growth carried out either directly on said thin support layer (13) or on an interposed layer (5, 23, 31, 32) transferred thereto; c) detaching said remainder (11) from the thin support layer (13) along the zone of weakness (12) by deliberately supplying external energy. Application to the field of optics, optoelectronics, or electronics.

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